



SEMICONDUCTOR

Shandong Yiguang Electronic Joint stock Co., Ltd

TECHNICAL DATA

S9014LT1

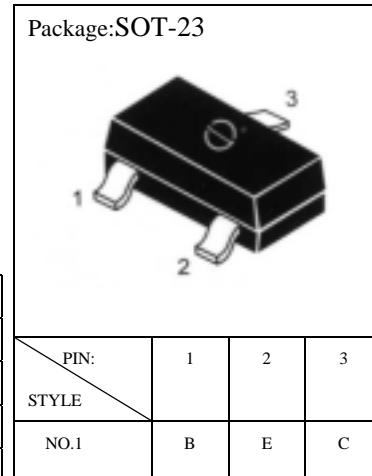
NPN EPITAXIAL SILICON TRANSISTOR

PRE-AMPLIFIER,LOW LEVEL&LOW NOISE

- * Complement to S9015LT1
- * Collector Current: $I_c = 100\text{mA}$
- * Collector-Emitter Voltage: $V_{ce} = 45\text{V}$
- * High Total Power Dissipation: $P_c = 225\text{mW}$
- * High H_f And Good Linearity

ABSOLUTE MAXIMUM RATINGS at $T_a=25$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	50	V
Collector-Emitter Voltage	V_{ceo}	45	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c	100	mA
Collector Dissipation $T_a=25^*$	P_D	225	mW
Junction Temperature	T_j	150	
Storage Temperature	T_{stg}	-55-150	

ELECTRICAL CHARACTERISTICS at $T_a=25$

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{cbo}	50			V	$I_c=100\mu\text{A}$ $I_e=0$
Collector-Emitter Breakdown Voltage#	BV_{ceo}	45			V	$I_c= 1\text{mA}$ $I_b=0$
Emitter-Base Breakdown Voltage	BV_{ebo}	5			V	$I_e= 100\mu\text{A}$ $I_c=0$
Collector-Base Cutoff Current	I_{cbo}			50	nA	$V_{cb}= 50\text{V}$ $I_e=0$
Emitter-Base Cutoff Current	I_{ebo}			50	nA	$V_{eb}= 5\text{V}$ $I_c= 0$
DC Current Gain	H_f	60	300	1000		$V_{ce}= 5\text{V}$ $I_c= 1\text{mA}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.3	V	$I_c= 100\text{mA}$ $I_b= 5\text{mA}$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			1.00	V	$I_c= 100\text{mA}$ $I_b= 5\text{mA}$
Base-Emitter on Voltage	$V_{be(on)}$	0.58	0.63	0.7	V	$V_{ce}= 5\text{V}$ $I_c= 2\text{mA}$
Output Capacitance	C_{ob}		2.2	3.5	PF	$V_{cb}= 10\text{V}$ $I_e=0$ $f=1\text{MHz}$
Current Gain-Bandwidth Product	f_T	150	270		MHz	$V_{ce}= 5\text{V}$ $I_c= 10\text{mA}$
Noise Figure	NF			10	dB	$V_{ce}= 5\text{V}$ $I_c= 0.2\text{mA}$ $f=1\text{KHz}$ $R_s=2\text{Kohm}$

* Total Device Dissipation : $FR=1 \times 0.75 \times 0.062 \text{in Board,Derate } 25^{\circ}\text{C}$.

Pulse Test : Pulse Width 300μS,Duty cycle 2%

DEVICE MARKING:

S9014LT1=L6



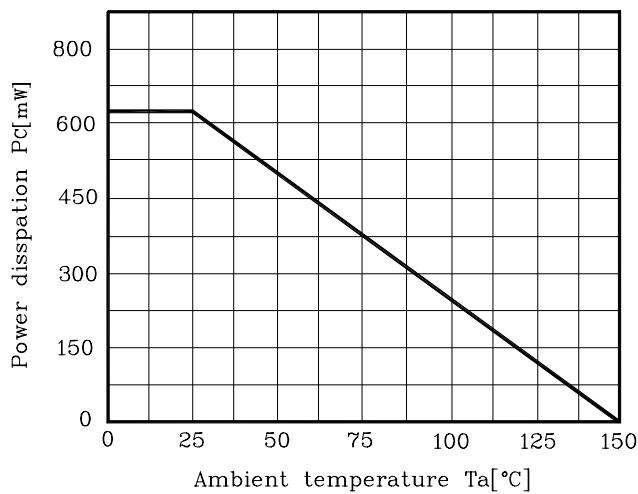
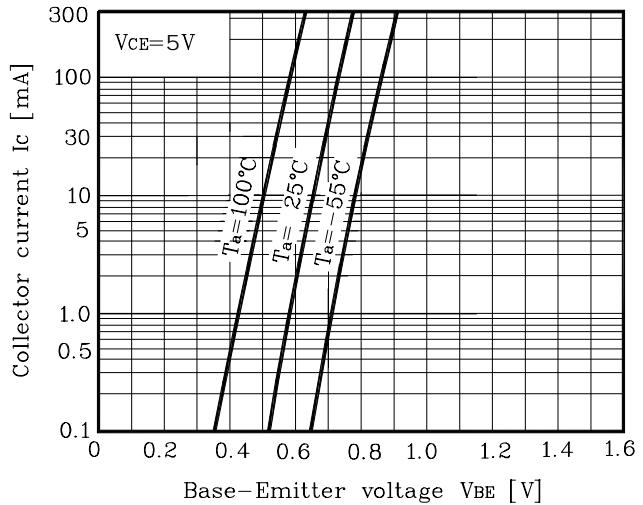
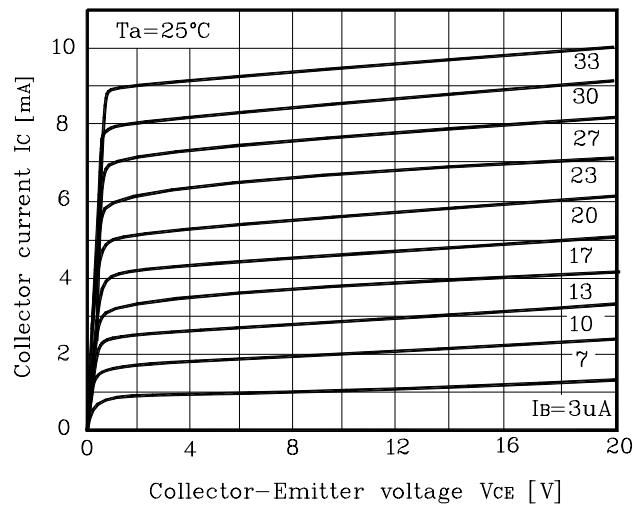
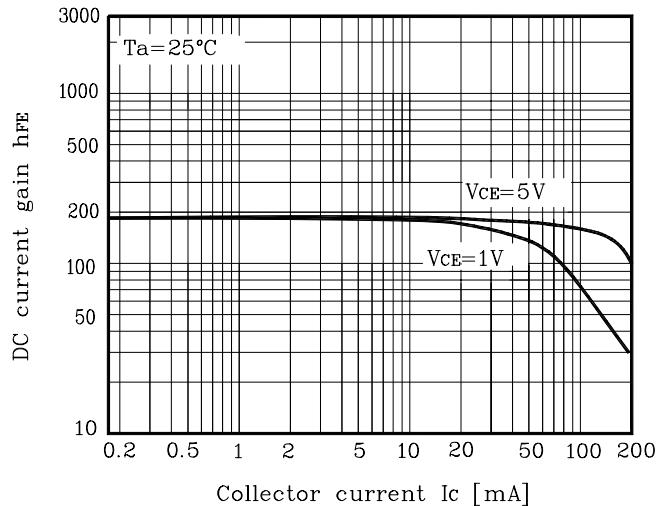
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Fig. 1 $P_c - T_a$ Fig. 2 $I_c - V_{BE}$ Fig. 3 $I_c - V_{CE}$ Fig. 4 $h_{FE} - I_c$ Fig. 5 $V_{CE(sat)} - I_c$ 